Ultra Low Noise, Low Current, Shutdown Monolithic Amplifier Die

PMA2-133LN-D+

50Ω 10 to 13 GHz

The Big Deal

- Ultra-low noise figure, 1.3 dB
- Low Current, 13 mA at 3V and 29mA at 5V
- Excellent ESD protection, Class 1C
- Shutdown feature

Product Overview

Mini-Circuits' PMA2-133LN-D+ is an E-PHEMT based, ultra-low noise MMIC amplifier die. The model offers a unique combination of low current consumption, low noise and high IP3, making it an ideal for sensitive, high-dynamic-range receiver applications. This design operates at both 3V & 5V supply, is well matched for 50Ω systems.

Key Features

Feature	Advantages	
Ultra-low noise, 1.3 dB at 11 GHz	Enables lower system noise figure performance.	
High IP3, 28.6 dBm typ. at 11 GHz	The combination of low noise and high IP3 makes the PMA2-133LN-D+ ideal for use in low noise receiver front end (RFE) as it gives the user the advantages of sensitivity and two-tone IM performance at both ends of the dynamic range.	
Support Low operating voltage, 3V&5V	Usable in battery operated systems.	
Low current consumption, 13 mA at 3V 29 mA at 5V	Enables prolonged battery life.	
Shutdown feature (Ven=0V, V_{DD} =3/5V)	Saves DC power consumption when it is not reguired.	
Separate pads for $V_{\mbox{\scriptsize DD}}$ and RF-OUT	Built-in RF-choke separates $V_{\mbox{\scriptsize DD}}$ and RF-OUT ports, minimizing external components, cost and saving PCB space.	
Excellent ESD protection, Class 1C	Robust ESD performance eliminates the need for external ESD protection circuits, sav- ing PCB space, minimizing noise figure degradation, and reducing cost.	
Unpackaged Die	Enables the user to integrate the amplifier directly into hybrids	



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Typical Applications

- Satellite communication
- Military Radar
- VSAT
- Point to Point
- Radio Astronomy



+RoHS Compliant The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

Ordering Information: Refer to Last Page

General Description

Mini-Circuits' PMA2-133LN-D+ is an E-PHEMT based, ultra-low noise MMIC amplifier die. The model offers a unique combination of low current consumption, low noise and high IP3, making it an ideal for sensitive, high-dynamic-range receiver applications. This design operates at both 3V & 5V supply, is well matched for 50Ω systems.

Simplified Schematic and Pad description



Pad #	Function	Description	
1	RF-OUT	RF Output pad. This pad requires the use of an external DC blocking capacitor.	
2	V _{DD}	DC Supply pad, Connect to external DC power supply.	
3	RF-IN	RF Input pad. This pad requires the use of an external DC blocking capacitor.	
4	Ven	Gain or shutdown model enable voltage pad. Connect to VDD for Gain mode opera- tion. Connect to Ground to shutdown the amplifier.	
Bottom of Die	GND	Connections to Ground.	

Bonding Pad Position



REV. OR M164787 PMA2-133LN-D+ WP/RS/CP 180620 Page 2 of 6

PMA2-133LN-D+

Electrical Specifications¹ at 25°C, 3V&5V, and 50 ohms unless noted

Parameter Frequency Range Noise Figure Gain Reverse Isolation Input Return Loss	Condition (GHz) 10.0 10.7 11.0 12.0 13.0 10.7 11.0 10.7 11.0 12.0 13.0 11.0 12.0 13.0 11.0 13.0 11.0 10.7 11.0 10.7 11.0 10.7 11.0 10.7 11.0 10.7 10.0 10.7 10.7	<u>Min.</u> 10	Typ. 1.4 1.4 1.4 1.4 1.4 1.5 1.6 14.1 14.1 14.1 14.1 14.1 14.1 14.1 14.3	<u>Max.</u> 13	Typ. 1.5 1.3 1.3 1.4 1.5 15.3 15.3 15.3 15.6 15.8 23.3	dB dB dB
Noise Figure Gain Reverse Isolation	10.7 11.0 12.0 13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7	10	1.4 1.4 1.5 1.6 14.1 14.1 14.1 14.1 14.0 22.7	13	1.3 1.3 1.4 1.5 15.3 15.3 15.3 15.6 15.8	dB
Gain Reverse Isolation	10.7 11.0 12.0 13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7		1.4 1.4 1.5 1.6 14.1 14.1 14.1 14.1 14.0 22.7		1.3 1.3 1.4 1.5 15.3 15.3 15.3 15.6 15.8	dB
Reverse Isolation	11.0 12.0 13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7		1.4 1.5 1.6 14.1 14.1 14.1 14.1 14.0 22.7		1.3 1.4 1.5 15.3 15.3 15.3 15.6 15.8	
Reverse Isolation	12.0 13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7		1.5 1.6 14.1 14.1 14.1 14.1 14.0 22.7		1.4 1.5 15.3 15.3 15.3 15.6 15.8	
Reverse Isolation	12.0 13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7		1.6 14.1 14.1 14.1 14.1 14.0 22.7		1.5 15.3 15.3 15.3 15.6 15.8	
Reverse Isolation	13.0 10.0 10.7 11.0 12.0 13.0 11.0 10.0 10.7		14.1 14.1 14.1 14.1 14.0 22.7		1.5 15.3 15.3 15.3 15.6 15.8	
Reverse Isolation	10.7 11.0 12.0 13.0 11.0 10.0 10.7		14.1 14.1 14.1 14.0 22.7		15.3 15.3 15.6 15.8	
	11.0 12.0 13.0 11.0 10.0 10.7		14.1 14.1 14.0 22.7		15.3 15.6 15.8	dB
	12.0 13.0 11.0 10.0 10.7		14.1 14.0 22.7		15.6 15.8	dB
	13.0 11.0 10.0 10.7		14.0 22.7		15.8	dB
	11.0 10.0 10.7		22.7			dB
	10.0 10.7				23.3	dB
Input Return Loss	10.7		13			
1	10.7				16	dB
			14		17	
	11.0		14		17	
	12.0		17		21	
	13.0		27		24	
Output Return Loss	10.0		18		14	dB
	10.7		16		12	
	11.0		16		12	
	12.0		26		18	
	13.0		13		18	
Output Power at 1dB Compression	10.0		8.4		13.3	dBm
	10.7		9.4		14.4	
	11.0		8.9		13.5	
	12.0		8.5		13.1	
	13.0		7.1		11.5	
Output IP3	10.0		23.4		27.9	dBm
Pout=-10 dBm/tone	10.7		23.7		29.3	
	11.0		23.6		28.6	
	12.0		23.8		28.8	
	13.0		23.5		28.9	
Device Operating Voltage (V _{DD}) ³	10.0		3.0		5.0	V
Device Operating Current (I _{DD})			13		29	mA
Device Current Variation vs. Temperature ²			-10		-53	µA/°C
Device Current Variation vs. Voltage			0.0079		0.0076	mA/mV
Thermal Resistance, junction-to-ground lead			124		118	°C/W

¹ Measured on Mini-Circuits Characterization test board. Die is packaged in 2x2 MCLP and soldered on TB-991+. See Characterization Test Circuit (Fig. 1) ² (Current at 85°C - Current at -45°C)/130 ³ V_{DD} is connected to Ven.

Absolute Maximum Ratings⁴

Parameter	Ratings	
Operating Temperature (ground lead)	-40°C to 85°C	
Total Power Dissipation	0.31W	
Input Power (CW)	+19 dBm (5minutes max) +10 dBm (continuous)	
DC Voltage	+7.7V	

Note: ⁴ Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

Recommended Application and Characterization Test Circuit



For Gain Mode Operation:

Component	Size	Value	Manufacturer	P/N
C1, C2	0402	0.1uF	Murata	GRM155R71C104KA88D
C3, C4	0402	100pF	Murata	GRM1555C1H101J01D
R1	0402	0 ohms	KOA	RK73Z1JTTD

Fig 1. Application and Characterization Circuit

This block diagram is used for DUT characterization in Gain Mode operation. (Die is packaged in 2x2mm MCLP and soldered on Mini-Circuits Characterization test board TB-991+). For DUT pad description, please see PMA2-133LN+ data sheet. Gain, Return loss, Output power at 1dB compression (P1dB), Output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm

2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, -10 dBm/tone at output.

Assembly Diagram



Assembly and Handling Procedure

- 1. Storage
 - Dice should be stored in a dry nitrogen purged desiccators or equivalent.
- 2. ESD

MMIC E-PHEMT amplifier dice are susceptible to electrostatic and mechanical damage. Die are supplied in antistatic protected material, which should be opened in clean room conditions at an appropriately grounded anti-static worksta tion. Devices need careful handling using correctly designed collets, vacuum pickup tips or sharp antistatic tweezers to deter ESD damage to dice.

3. Die Attach

The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are DieMat DM6030HK-PT/H579 or Ablestik 84-1LMISR4. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total die periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. It is recommended to use antistatic die pick up tools only.

4. Wire Bonding

Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermosonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1 mil diameter. Bonds must be made from the bond pads on the die to the package or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.

Additional Detailed Technic additional information is available on our				
	Data Table	Data Table		
Performance Data	Swept Graphs			
	S-Parameter (S2P Files) Data Set with and without port extension(.zip file)			
Case Style	Die			
	Quantity, Package	Model No.		
Die Ordering and packaging information	Small, Gel - Pak: 5,10,50,100 KGD* Medium [†] , Partial wafer: KGD*<800 Large [†] , Full Wafer	PMA2-133LN-DG+ PMA2-133LN-DP+ PMA2-133LN-DF+		
momaton	[†] <i>Available upon request contact sales representative</i> Refer to AN-60-067			
Environmental Ratings	ENV80			

*Known Good Dice ("KGD") means that the dice in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such dice fall within a predefined range. While DC testing is not definitive, it does help to provide a higher degree of confidence that dice are capable of meeting typical RF electrical parameters specified by Mini-Circuits.

ESD Rating**

Human Body Model (HBM): Class 1C (pass 1000V) in accordance with ANSI/ESD STM 5.1 - 2001

** Tested in industry standard 2mm x 2mm MCLP

Additional Notes

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
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